



60V N-CHANNEL ENHANCEMENT MODE MOSFET POWERDI

Product Summary

V _{(BR)DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
2014	$10m\Omega$ @ $V_{GS} = 10V$	34A
60V	11.7m Ω @ $V_{GS} = 4.5V$	31.5A

Description

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$), yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- Backlighting
- Power Management Functions
- DC-DC Converters

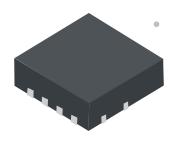
Features and Benefits

- Low R_{DS(ON)} Ensures On-State Losses Are Minimized
- Excellent Q_{gd} x R_{DS(ON)} Product (FOM)
- Advanced Technology for DC-DC Converters
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- 100% UIS (Avalanche) Rated
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

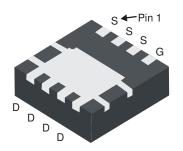
Mechanical Data

- Case: POWERDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.008 grams (Approximate)

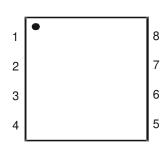
POWERDI3333-8



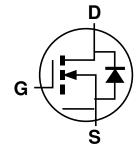
Top View



Bottom View



Top View Internal Schematic



Equivalent Circuit

Ordering Information (Note 4)

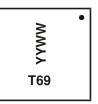
Part Number	Case	Packaging
DMT6009LFG-7	POWERDI3333-8	2,000/Tape & Reel
DMT6009LFG-13	POWERDI3333-8	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and
- <1000ppm antimony compounds.</p>
 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.



Marking Information



T69 = Product Type Marking Code YYWW = Date Code Marking YY = Last Digit of Year (ex: 15 = 2015) WW = Week Code (01 to 53)

Maximum Ratings $(@T_A = +25^{\circ}C, \text{ unless otherwise specified.})$

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	60	V	
Gate-Source Voltage	V _{GSS}	±16	V	
Continuous Drain Current (Note 5) V _{GS} = 10V	$T_C = +25^{\circ}C$ $T_C = +70^{\circ}C$	I _D	34 27	А
Continuous Drain Current (Note 5) $V_{GS} = 10V$ $ T_A = +25^{\circ}C $ $ T_A = +70^{\circ}C $		ID	11 9	А
Maximum Continuous Body Diode Forward Current (Note 5)	I _S	2.4	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	90	Α	
Avalanche Current, L=0.1mH	I _{AS}	28.6	Α	
Avalanche Energy, L=0.1mH	E _{AS}	40.8	mJ	

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5) $T_A = +25^{\circ}C$		P_{D}	2.08	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\theta JA}$	60	°C/W
Total Power Dissipation (Note 5) $T_C = +25^{\circ}C$		P_{D}	19.2	W
Thermal Resistance, Junction to Case (Note 5)		Rejc	6.5	°C/W
Operating and Storage Temperature Range		$T_{J_i} T_{STG}$	-55 to +150	°C

Note: 5. ReJA is determined with the device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate. ReJC is guaranteed by design while ReJA is determined by the user's board design.

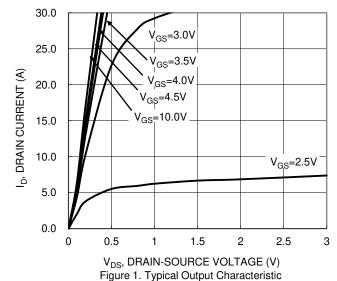


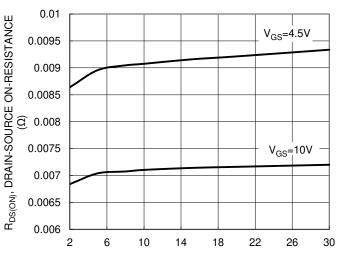
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV _{DSS}	60	_		٧	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}		_	1	μΑ	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 16V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	$V_{GS(TH)}$	0.7	_	2	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance		1	_	10	mΩ	$V_{GS} = 10V, I_D = 13.5A$	
Static Dialii-Source Off-Nesistance	R _{DS(ON)}	I		11.7		$V_{GS} = 4.5V, I_D = 11.5A$	
Diode Forward Voltage	V_{SD}	I	_	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	C _{iss}		1,925	_		$V_{DS} = 30V$, $V_{GS} = 0V$, $f = 1MHz$	
Output Capacitance	Coss	1	438		pF		
Reverse Transfer Capacitance	C_{rss}	I	41	l			
Gate Resistance	R_{g}	1	1.7		Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Q_g	1	15.6	_	nC Vps = 30V, lp = 13.5A		
Total Gate Charge (V _{GS} = 10V)	Q_g	I	33.5	l			
Gate-Source Charge	Q_{gs}	1	4.7	_	110	$V_{DS} = 30V, I_D = 13.5A$	
Gate-Drain Charge	Q_{gd}	1	5.3	_			
Turn-On Delay Time	t _{D(ON)}	_	4.5	_			
Turn-On Rise Time	t _R	_	8.6	_	200	$V_{DD} = 30V, V_{GS} = 10V,$ $R_G = 6\Omega, I_D = 13.5A$	
Turn-Off Delay Time	t _{D(OFF)}	_	35.9	_	ns		
Turn-Off Fall Time	t _F	_	15.7	_			
Body Diode Reverse Recovery Time	t _{RR}		18.2	_	ns	1 10 50 41/44 1000/	
Body Diode Reverse Recovery Charge	Q _{RR}	_	33.1	_	nC	$\frac{1}{nC}$ I _F = 13.5A, di/dt = 400A/µs	

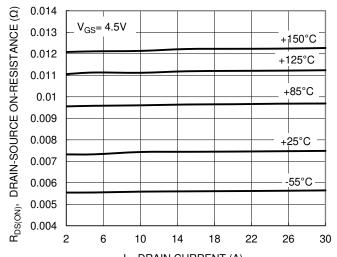
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing. Notes:



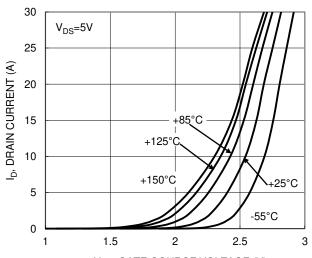




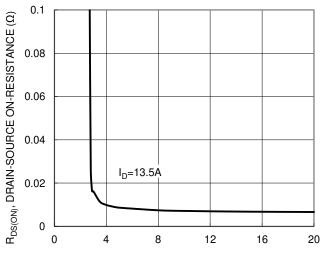
I_D, DRAIN-SOURCE CURRENT (A) Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage



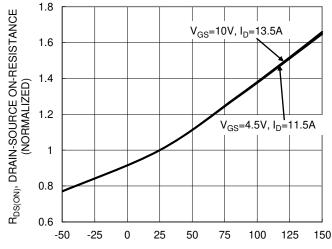
I_D, DRAIN CURRENT (A) Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature



 $\rm V_{GS}$, GATE-SOURCE VOLTAGE (V) Figure 2. Typical Transfer Characteristic



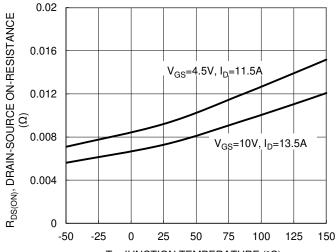
V_{GS}, GATE-SOURCE VOLTAGE (V) Figure 4. Typical Transfer Characteristic



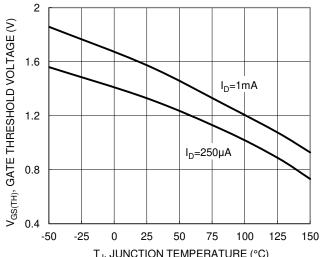
T_J, JUNCTION TEMPERATURE (°C) Figure 6. On-Resistance Variation with Junction Temperature



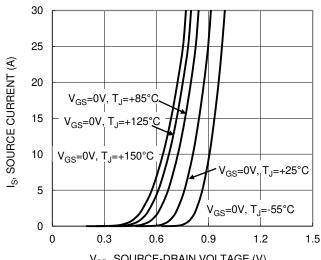




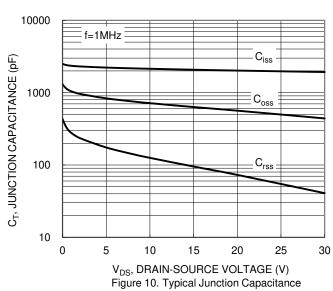
 $\rm T_{J},\,JUNCTION\,TEMPERATURE\,(^{\circ}C)$ Figure 7. On-Resistance Variation with Junction Temperature



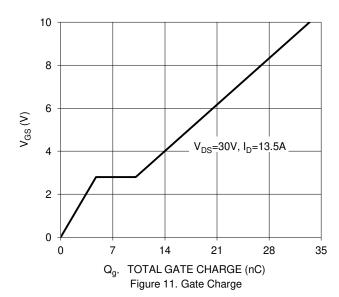
 $\mathsf{T_{J}},\mathsf{JUNCTION}$ TEMPERATURE (°C) Figure 8. Gate Threshold Variation vs. Junction Temperature



V_{SD}, SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current



1000 $R_{DS(ON)}$ Limited 100 ID, DRAIN CURRENT (A) 10 P_W=10ms ∰ P_W=100ms 0.1 $T_{J(MAX)}$ =150°C T_A =25°C P_W=10s 0.01 Single Pulse DUT on 1*MRP board 0.001 0.01 V_{DS} , DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area



100

10



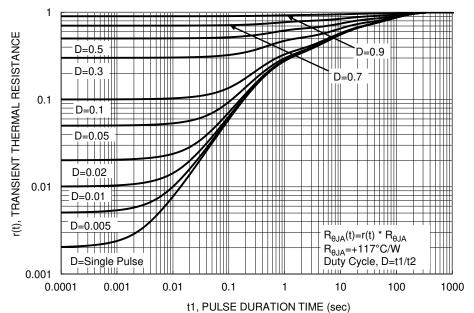


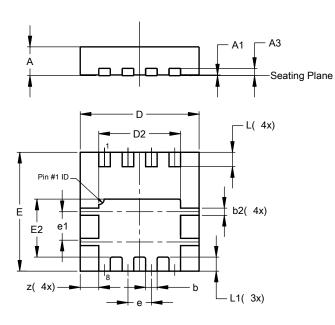
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

POWERDI3333-8

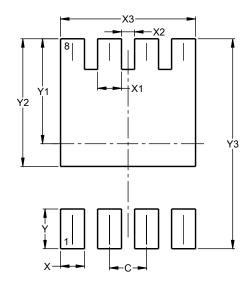


POWERDI3333-8						
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05	0.02			
A3	_	_	0.203			
b	0.27	0.37	0.32			
b2	_	_	0.20			
D	3.25	3.35	3.30			
D2	2.22	2.32	2.27			
Е	3.25	3.35	3.30			
E2	1.56	1.66	1.61			
е	_	_	0.65			
e1	0.79	0.89	0.84			
L	0.35	0.45	0.40			
L1	_	_	0.39			
Z	_	_	0.515			
All Dimensions in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

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Dimensions	Value (in mm)		
С	0.650		
X	0.420		
X1	0.420		
X2	0.230		
Х3	2.370		
Υ	0.700		
Y1	1.850		
Y2	2.250		
V٦	3 700		



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